TOSHIBA Photocoupler Infrared LED + Photo IC

TLP550

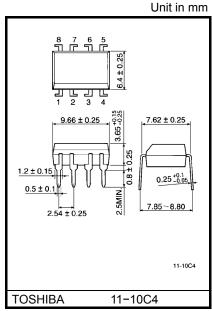
Digital Logic Isolation
Line Receiver Feedback Control
Power Supply Control
Switching Power Supply
Transistor Inverter

TLP550 constructs a high emitting diode and a one chip photo diodetransistor.

TLP550 has no base connection, and is suitable for application at noisy environmental condition.

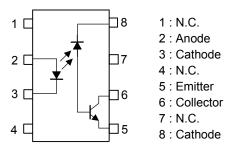
This unit is 8-lead DIP package.

- Isolation voltage: 2500 Vrms (min.)
- Switching speed: t_{pHL} , $t_{pLH} = 0.5\mu s$ (typ.)(RL=1.9 k Ω)
- TTL compatible
- UL recognized: UL1577, file No. E67349

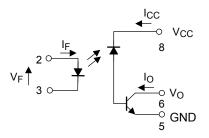


Weight: 0.54 g (typ.)

Pin Configuration (top view)



Schematic



Current Transfer Ratio

| Classification | | sfer Ratio (%) /IF) | Marking of Classificatio | | |
|----------------|-----|------------------------|--------------------------|--|--|
| | MIN | MAX | | | |
| (None) | 10 | _ | Blank, O, Y | | |
| Rank O | 19 | _ | 0 | | |
| Rank Y | 35 | _ | Υ | | |

Absolute Maximum Ratings (Ta = 25°C)

| | Characteristic | | Symbol | Rating | Unit |
|-------------|--|----------|------------------|---------|------|
| | Forward current | (Note 1) | l _F | 25 | mA |
| TED | Pulse forward current | (Note 2) | I _{FP} | 50 | mA |
| | Peak transient forward current | (Note 3) | I _{FPT} | 1 | А |
| | Reverse voltage | | V_{R} | 5 | V |
| | Diode power dissipation | (Note 4) | P_{D} | 45 | mW |
| | Output current | | ΙO | 8 | mA |
| ١. | Peak output current | | I _{OP} | 16 | mA |
| Detector | Supply voltage | | V_{CC} | -0.5~15 | V |
| Det | Output voltage | | VO | -0.5~15 | V |
| | Output power dissipation | (Note 5) | PO | 100 | mW |
| Оре | erating temperature range | | T _{opr} | -55~100 | °C |
| Sto | Storage temperature range | | T _{stg} | -55~125 | °C |
| Lea | Lead solder temperature (10s) | | | 260 | °C |
| Isol (AC | Isolation voltage (AC, 1min., R.H. = 40~60%) (Note | | BVS | 2500 | Vrms |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

2

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Derate 0.8mA above 70°C.

(Note 2) 50% duty cycle, 1ms pulse width. Derate 1.6mA / °C above 70°C.

(Note 3) Pulse width 1µs, 300pps.

(Note 4) Derate 0.9mW / °C above 70°C.

(Note 5) Derate 2mW / $^{\circ}\text{C}$ above 70 $^{\circ}\text{C}.$

Electrical Characteristics (Ta = 25°C)

| Characteristic | | Symbol | Test condition | | Min. | Тур. | Max. | Unit | |
|----------------|---|---------------------------------|--|-------------|------------|------|------------------|------|---------|
| | Forward voltage | V _F | I _F = 16 mA | | | 1.45 | 1.65 | 1.85 | V |
| LED | Forward voltage temperature coefficient | ΔV _F /ΔTa | I _F = 16 mA | | | _ | -2 | 1 | mV / °C |
| | Reverse current | I _R | V _R = 5 V | | | _ | ı | 10 | μΑ |
| | Capacitance between terminal | C _T | V _F = 0, f = 1MHz | | | _ | 60 | - | pF |
| Detector | High level output current | I _{OH (1)} | $I_F = 0 \text{ mA}, V_{CC} = V_O = 5.5 \text{ V}$ | | | _ | 3 | 500 | nA |
| | | I _{OH} (2) | I _F = 0 mA, V _{CC} = V _O = 15 V | | | _ | _ | 5 | μΑ |
| | | Іон | $I_F = 0 \text{ mA}, V_{CC} = V_O = 15 \text{ V}$ Ta = 70°C | | | _ | _ | 50 | μΑ |
| | High level supply voltage | ICCH | I _F = 0 mA, V _{CC} = 15 V | | _ | 0.01 | 1 | μΑ | |
| | Current transfer ratio | I _O / I _F | I _F = 16 mA V _{CC} = 4.5 V V _O = 0.4 V | Ta = 25°C | | 10 | 30 | _ | |
| | | | | | Rank: 0 | 19 | 30 | _ | % |
| | | | | | Rank : Y | 35 | 50 | | |
| Coupled | | | | Ta = 0~70°C | | 5 | 1 | l | |
| | | | | | Rank: 0, Y | 15 | 1 | ı | |
| | Low level output voltage | V _{OL} | I_F = 16 mA, V_{CC} = 4.5 V I_O = 1.1 mA (rank 0: I_O = 2.4mA) | | _ | _ | 0.4 | V | |
| | Isolation resistance | R _S | R.H. = 40~60%, V = 1kV DC (Note 6) | | | _ | 10 ¹² | _ | Ω |
| | Capacitance between input to output | CS | V = 0, f = 1MHz | | | _ | 0.8 | | pF |

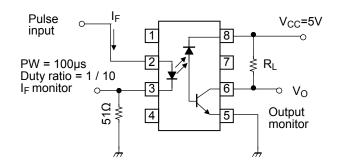
Switching Characteristics (Ta = 25°C)

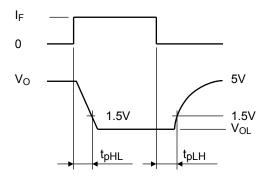
| Characteristic | Symbol | Test Condition | Min. | Тур. | Max. | Unit | |
|---|------------------|---|-----------|-------|------|-------|--|
| Propagation delay time | t _{pHL} | $I_F = 0 \rightarrow 16$ mA, $V_{CC} = 5V$, $R_L = 4.1$ kΩ | _ | 0.3 | 0.8 | μs | |
| (H→ L) | | (Note 7) Rank 0: R _L = 1.9 k | - Ω | 0.5 | 0.8 | | |
| Propagation delay time | . | I_F = 16 \rightarrow 0 mA, V_{CC} = 5V, R_L = 4.1 kΩ | _ | 1.0 | 2.0 | μs | |
| $(L \rightarrow H)$ | t _{pLH} | (Note 7) Rank 0: R _L = 1.9 k | - Ω | 0.6 | 1.2 | μδ | |
| Common mode transient immunity at high output level | | I_F = 0 mA, V_{CM} = 200 V_{p-p} R_L = 4.1 kΩ (rank 0: R_L = 1.9 kΩ) (Not | — e 8) | 1500 | _ | V /µs | |
| Common mode transient immunity at low output level | C _{ML} | I_F = 16 mA, V_{CM} = 200 V_{p-p} R_L = 4.1 kΩ (rank 0: R_L = 1.9 kΩ) (Note | — e 8) | -1500 | | V /µs | |

(Note 6) Device considered two-terminal device: Pins 1, 2, 3 and 4 shorted together and pin 5, 6, 7 and 8 shorted together.

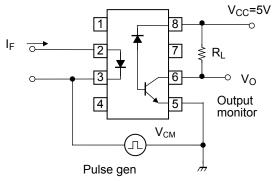
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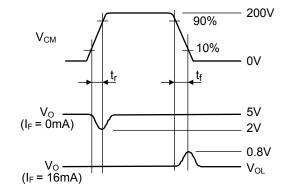
(Note 7) Switching time test circuit.





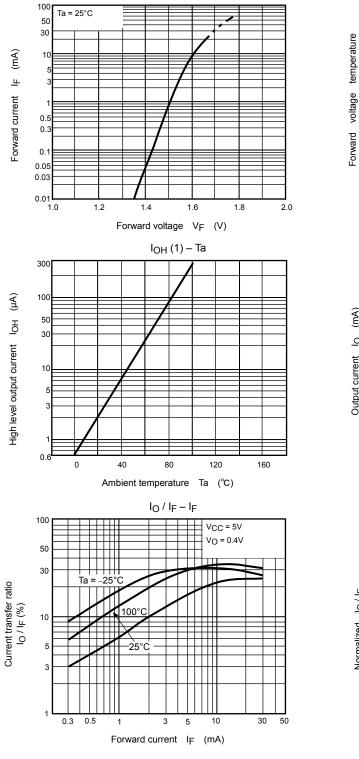
(Note 8) Common mode transient immunity test circuit.



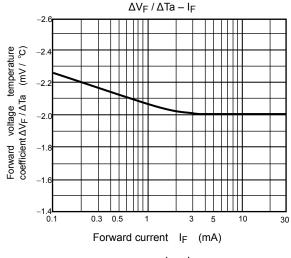


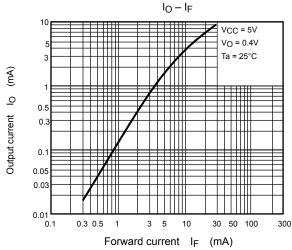
$$Z_{O}$$
=50 Ω CM_{H} = $\frac{160 \text{ (V)}}{t_{f} (\mu \text{s})}$, CM_{L} = $\frac{160 \text{ (V)}}{t_{f} (\mu \text{s})}$

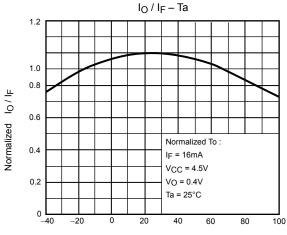
(Note 9) Maximum electrostatic discharge voltage for any pins: 100V (C = 200pF, R = 0)



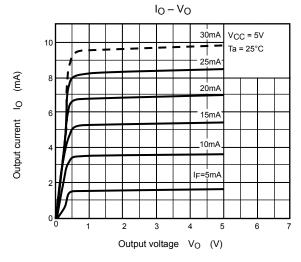
I_F – V_F

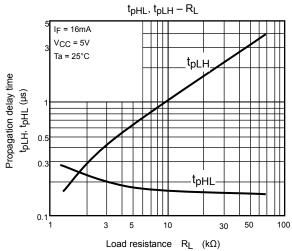


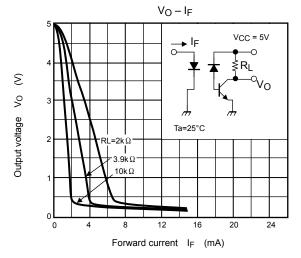




Ambient temperature Ta (°C)







6 2007-10-01

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